50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

14 September 2018

Product data sheet

## 1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in an ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs
- · Low package height of 0.5 mm
- AEC-Q101 qualified

## 3. Applications

- · Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- · Control of IC inputs
- Switching loads

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor, for the PNP transistor with negative polarity								
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V		
Io	output current			-	-	100	mA		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		80	-	-			
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ		
R2/R1	bias resistor ratio		[1]	1.7	2.13	2.6			

[1] See section "Test information" for resistor calculation and test conditions.



## 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	7 6	
3	O2	output (collector) TR2	5	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input (base) TR2	3 8 4	R2 R1
6	01	output (collector) TR1		
7	O1	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN1412-6 (SOT1268)	GND1 I1 O2 aaa-007379

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
PRMD16		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268			

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PRMD16	B7

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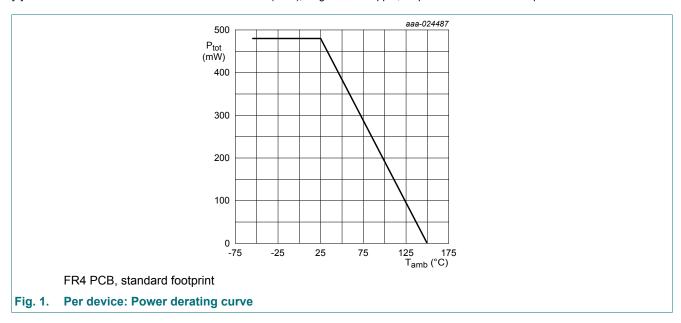
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	h negative polarity				
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	7	V
VI	input voltage	positive		-	40	V
		negative		-	-7	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
Per device			•			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

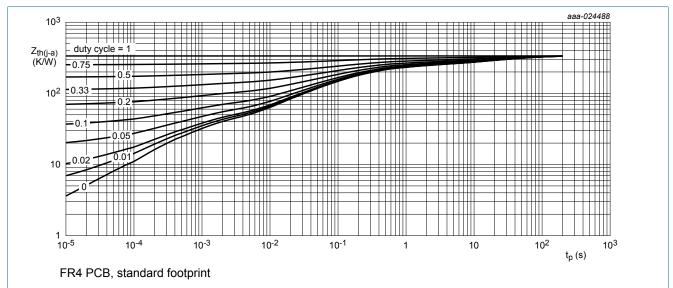


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
I <sub>CEO</sub>		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	1	μΑ
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	50	μΑ
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	120	μA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C		80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	0.8	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = 0.3 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C		2	1.1	-	V
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	1.7	2.13	2.6	
C <sub>C</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
		$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C		-	230	-	MHz
				-	180	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.

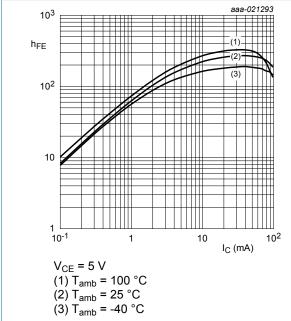


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

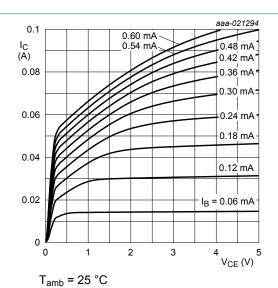
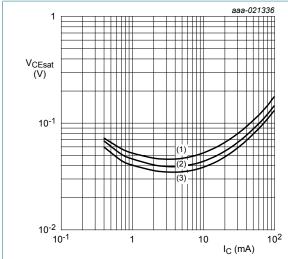


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

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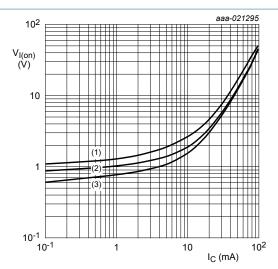


$$I_{\rm C}/I_{\rm B} = 10$$

$$(1) T_{amb} = 100 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 5. **NPN** transistor: Collector-emitter saturation voltage as a function of collector current; typical values

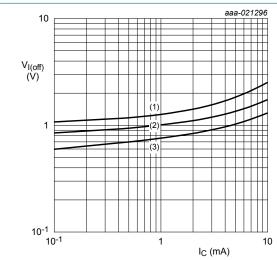


$$V_{CE} = 0.3 V$$

$$(1) T_{amb} = -40 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



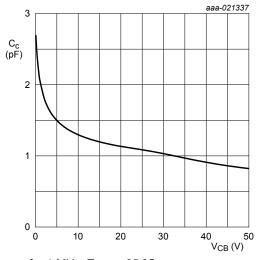
$$V_{CE} = 5 V$$

$$(1) T_{amb} = -40 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

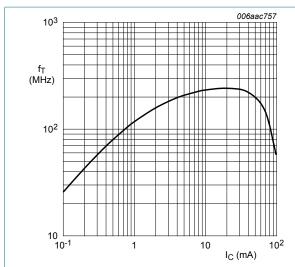
Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

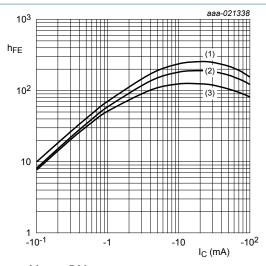
Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical

### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



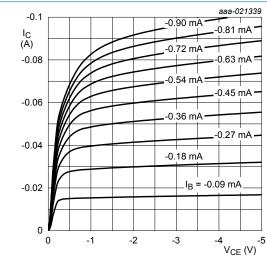
 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



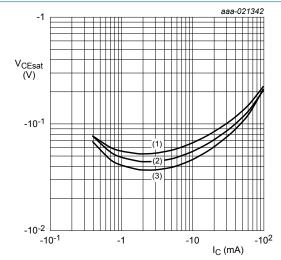
V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb}$  = 100 °C

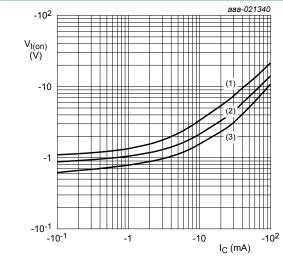
(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

-10

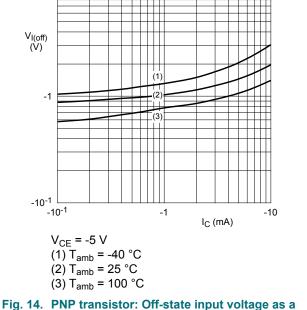
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 $V_{CE}$  = -0.3 V

(1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



function of collector current; typical values

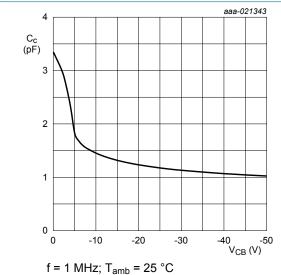
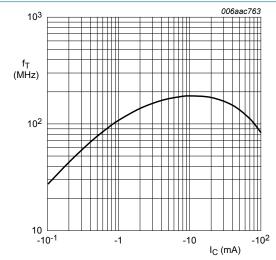


Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE}$  = -5 V;  $T_{amb}$  = 25 °C

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

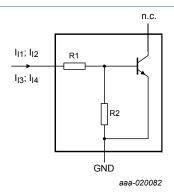


Fig. 17. NPN transistor: Resistor test circuit

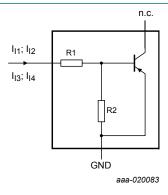


Fig. 18. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

#### **Table 8. Resistor test conditions**

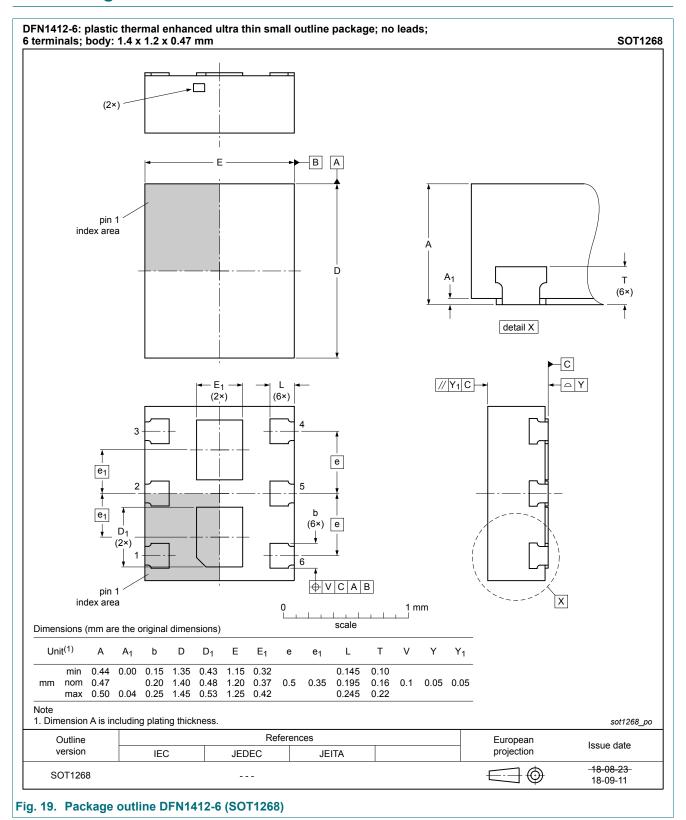
Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I <sub>I1</sub>	I <sub>12</sub>	I <sub>I3</sub>	I <sub>14</sub>
22	47	90 µA	140 µA	-55 µA	-105 μA

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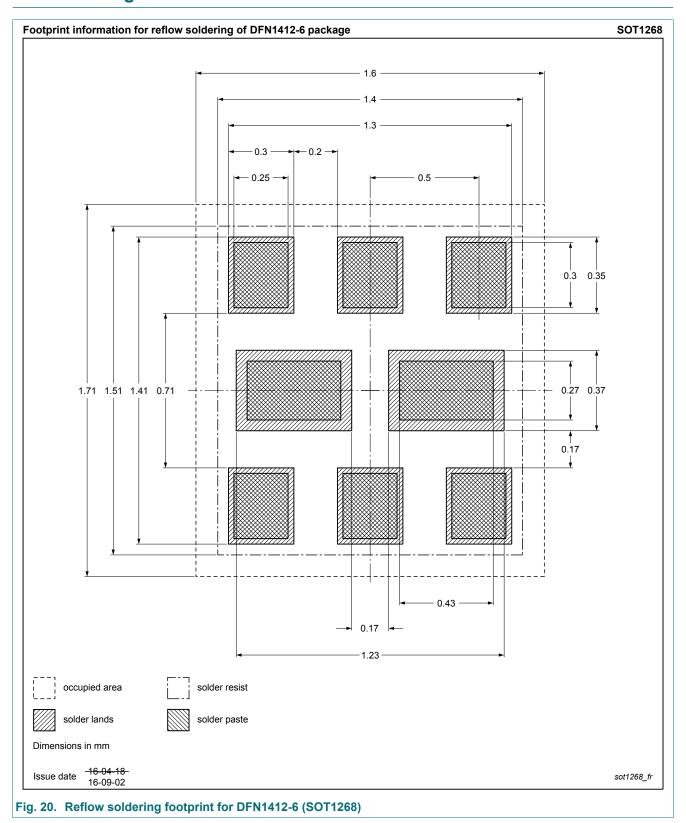
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# 12. Package outline



## 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 13. Soldering



## 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 14. Revision history

### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PRMD16 v.2	20180914	Product data sheet	-	PRMD16 v.1			
Modifications:	Package outli	Package outline drawing updated: Unit T added					
PRMD16 v.1	20170729	Product data sheet	-	-			

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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